



SHEET 1 OF 1

Form PTO 1449
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LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Yukihiko NAKATA, et al.

FILING DATE

September 30, 2003

GROUP

1753

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AV	Y. NAKATA, et al., Proceedings of Int. Conf. on Rapid Thermal Proceeding for Future Semiconductor Device, 2 pages, "RAPID-LOW-TEMPERATURE PHOTO-OXIDATION PROCESSING FOR ADVANCED POLY-SI TFTS", 2001
	AW	Y. NAKATA, et al., Extended Abstracts of International Workshop on Gate Insulator, pages 120-123, "PHOTO-OXIDATION AND PECVD STACKED GATE INSULATOR FOR POLY-SI TFTS AT 200-300 °C", November 1-2, 2001
	AX	Y. NAKATA, et al., Asia Display/DW '01, pages 376-378, "LOW-TEMPERATURE GATE INSULATOR FOR POLY-SI TFTS BY COMBINATION OF PHOTO OXIDATION AND PECVD", October 16-19, 2001
RRB	AY	Y. NAKATA, et al., Spring 48 th Applied Physics Related Joint Lecture Meeting, page 89, "LOW-TEMPERATURE OXIDE FORMATION FOR POLY-SI TFT BY PLASMA AND LIGHT PROCESS", 2001
	AZ	Y. NAKATA, et al., IEICE Transactions on Electronics, vol. E85-C, no. 11, pages 1849-1853, "LOW-TEMPERATURE GATE INSULATOR FOR POLY-SI THIN FILM TRANSISTORS BY COMBINATION OF PHOTO-OXIDATION AND PLASMA ENHANCED CHEMICAL VAPOR DEPOSITION USING TETRAETHYLOXOSILICATE AND O ₂ GASES", November 2002
		<input type="checkbox"/> Additional References sheet(s) attached

Examiner

R Buhl

Date Considered 2-2006

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.